

NTK3142P

Small Signal MOSFET

-20 V, -280 mA, P-Channel with ESD Protection, SOT-723

Features

- Enables High Density PCB Manufacturing
- 44% Smaller Footprint than SC-89 and 38% Thinner than SC-89
- Low Voltage Drive Makes this Device Ideal for Portable Equipment
- Low Threshold Levels, 1.8 V $R_{DS(on)}$ Rating
- Low Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics
- Operated at Standard Logic Level Gate Drive, Facilitating Future Migration to Lower Levels Using the Same Basic Topology.
- This is a Pb-Free Device

Applications

- Interfacing, Switching
- High Speed Switching
- Cellular Phones, PDA's

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	-20	V
Gate-to-Source Voltage		V_{GS}	± 8.0	V
Continuous Drain Current (Note 1)	Steady State	I_D	$T_A = 25^\circ\text{C}$	-260
			$T_A = 85^\circ\text{C}$	-185
	$t \leq 5 \text{ s}$	$T_A = 25^\circ\text{C}$	-280	mA
Power Dissipation (Note 1)	Steady State	P_D	$T_A = 25^\circ\text{C}$	400
			$t \leq 5 \text{ s}$	500
Continuous Drain Current (Note 2)	Steady State	I_D	$T_A = 25^\circ\text{C}$	-215
			$T_A = 85^\circ\text{C}$	-155
Power Dissipation (Note 2)	Steady State	P_D	$T_A = 25^\circ\text{C}$	280
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	-310	mA
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode) (Note 2)		I_S	-240	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)
2. Surface-mounted on FR4 board using the minimum recommended pad size.

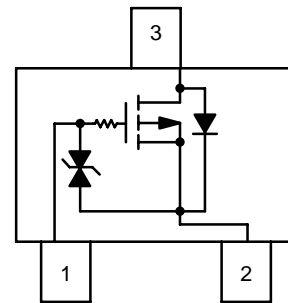


ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D Max
-20 V	2.7 Ω @ -4.5 V	-280 mA
	4.1 Ω @ -2.5 V	
	6.1 Ω @ -1.8 V	

SOT-723 (3-LEAD)

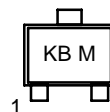


Top View
 1 - Gate
 2 - Source
 3 - Drain



CASE 631AA
SOT-723

MARKING DIAGRAM



KB = Specific Device Code
 M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NTK3142PT1G	SOT-723 (Pb-Free)	4000/Tape & Reel 4 mm Pitch
NTK3142PT5G	SOT-723 (Pb-Free)	8000/Tape & Reel 2 mm Pitch

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTK3142P

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	315	°C/W
Junction-to-Ambient – $t = 5$ s (Note 3)	$R_{\theta JA}$	250	
Junction-to-Ambient – Steady State Minimum Pad (Note 4)	$R_{\theta JA}$	440	

- Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)
- Surface-mounted on FR4 board using the minimum recommended pad size.

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = -100$ μA	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = -100$ μA , Reference to 25°C		14		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0$ V, $V_{DS} = -16$ V			-1	μA
		$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			20	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 5$ V			± 1	μA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = -250$ μA	-0.4		-1.3	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-2.0		mV/°C
Drain-to-Source On Resistance	$R_{DS(ON)}$	$V_{GS} = -4.5$ V, $I_D = -260$ mA		2.9	4.0	Ω
Drain-to-Source On Resistance	$R_{DS(ON)}$	$V_{GS} = -4.5$ V, $I_D = -10$ mA		2.7	3.4	Ω
		$V_{GS} = -2.5$ V, $I_D = -1$ mA		4.1	5.3	
		$V_{GS} = -1.8$ V, $I_D = -1$ mA		6.1	10	
Forward Transconductance	g_{FS}	$V_{DS} = -5$ V, $I_D = -10$ mA		73		mS

CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0$ V, $f = 1$ MHz, $V_{DS} = -10$ V		15.3		pF
Output Capacitance	C_{OSS}			4.3		
Reverse Transfer Capacitance	C_{RSS}			2.3		

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5$ V (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5$ V, $V_{DD} = -5$ V, $I_D = -100$ mA, $R_G = 6$ Ω		8.4	16	ns
Rise Time	t_r			15.3	28	
Turn-Off Delay Time	$t_{d(OFF)}$			37.5	80	
Fall Time	t_f			22.7	43	

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0$ V, $I_S = -10$ mA	$T_J = 25^\circ\text{C}$	0.69	-1.2	V
			$T_J = 125^\circ\text{C}$	0.56		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0$ V, $V_{DD} = -20$ V, $dI_{SD}/dt = 100$ A/ μs , $I_S = -1.0$ A		37	80	ns
Charge Time	t_a			15.9	30	
Discharge Time	t_b			21.1	50	
Reverse Recovery Charge	Q_{RR}			20	70	

- Pulse Test: pulse width ≤ 300 μs , duty cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

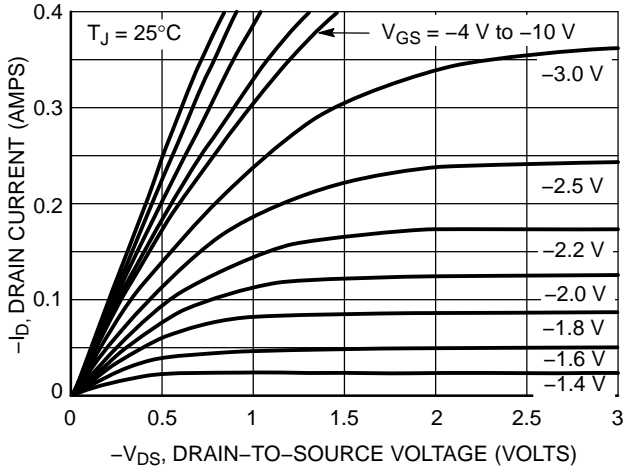


Figure 1. On-Region Characteristics

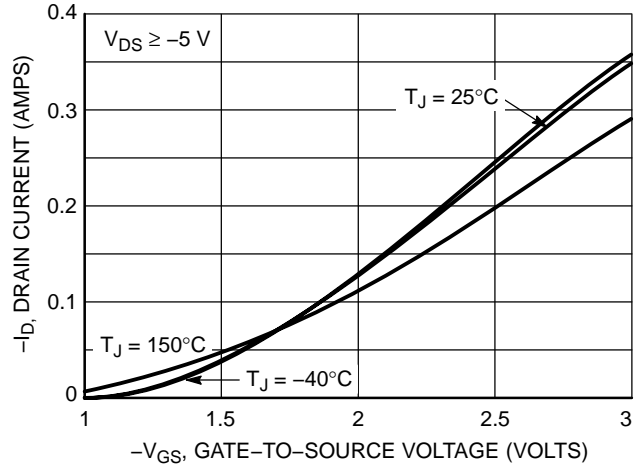


Figure 2. Transfer Characteristics

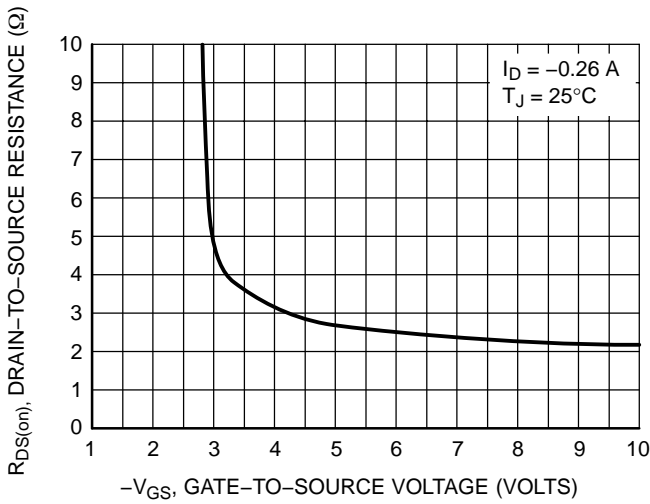


Figure 3. On-Resistance vs. Gate-to-Source Voltage

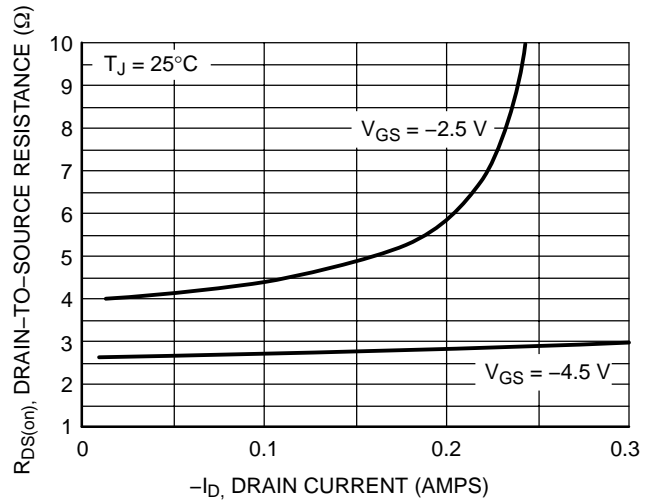


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

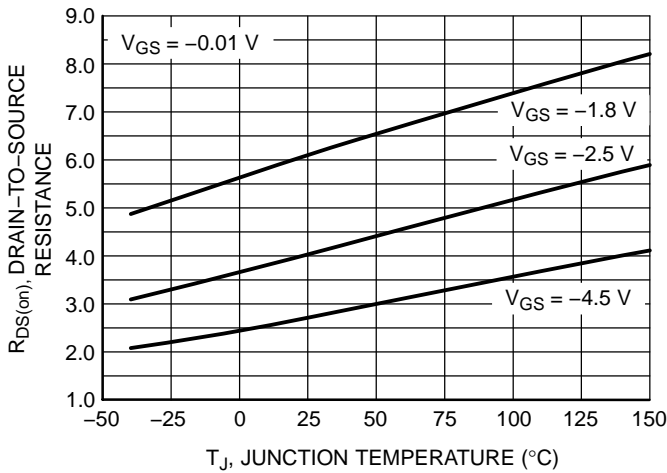


Figure 5. On-Resistance Variation with Temperature

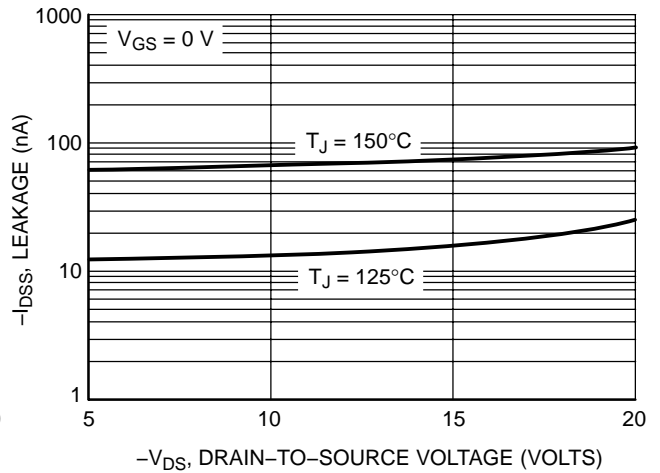


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

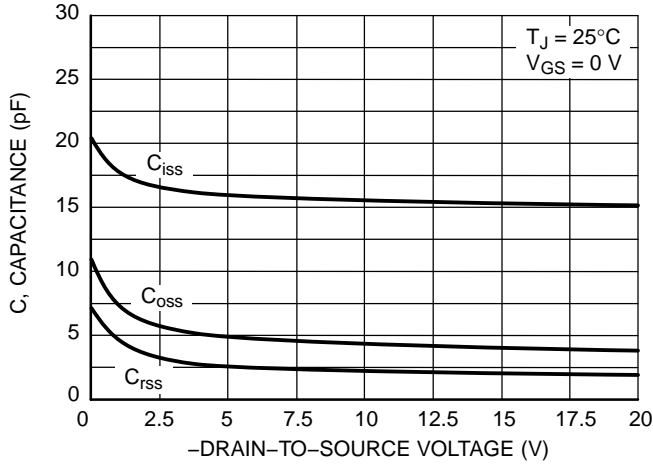


Figure 7. Capacitance Variation

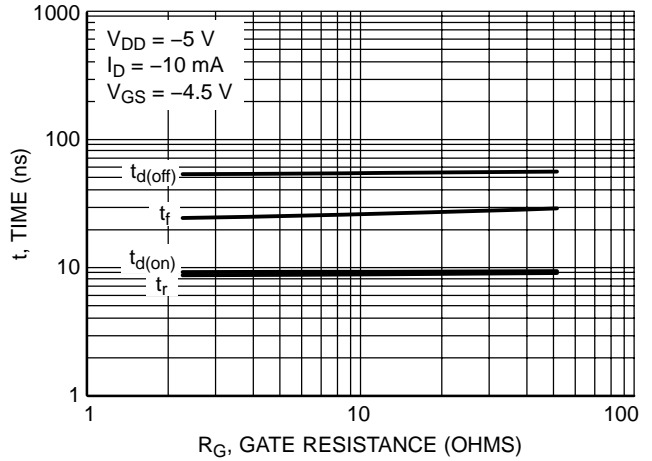


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

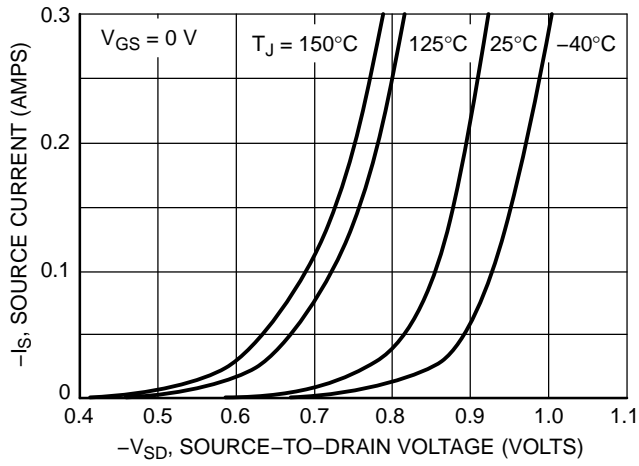
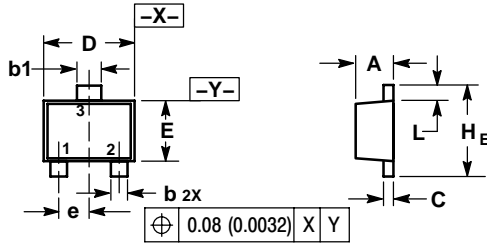


Figure 9. Diode Forward Voltage vs. Current

NTK3142P

PACKAGE DIMENSIONS

SOT-723
CASE 631AA-01
ISSUE B



NOTES:

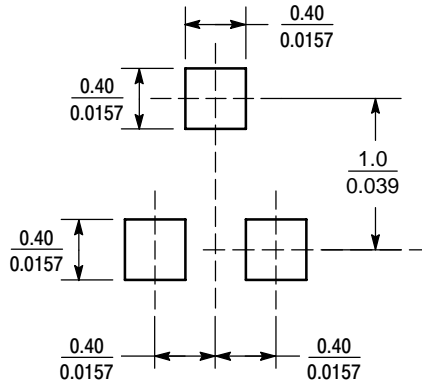
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
b	0.15	0.21	0.27	0.0059	0.0083	0.0106
b1	0.25	0.31	0.37	0.010	0.012	0.015
C	0.07	0.12	0.17	0.0028	0.0047	0.0067
D	1.15	1.20	1.25	0.045	0.047	0.049
E	0.75	0.80	0.85	0.03	0.032	0.034
e	0.40 BSC			0.016 BSC		
H E	1.15	1.20	1.25	0.045	0.047	0.049
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

STYLE 3:

1. ANODE
2. ANODE
3. CATHODE

SOLDERING FOOTPRINT*



SCALE 20:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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